

Amendments to the Claims

Claims 1-40 (Canceled)

41. (Currently amended) A transistor structure, comprising:

a gate oxide layer on a semiconductive substrate, the gate oxide layer comprising silicon dioxide and having a total thickness of 5 Angstroms; the gate oxide layer having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;

a conductive layer on the gate oxide layer; and

source/drain regions within the semiconductive substrate; the source/drain regions being gatedly connected to one another by the conductive layer.

42. (Original) The structure of claim 41 wherein the conductive layer comprises conductively-doped silicon.

43. (Original) The structure of claim 41 wherein the conductive layer comprises p-type conductively-doped silicon.

Claims 44-52 (Canceled)